

**TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT**  
**(Under 37 CFR 1.97(b) or 1.97(c))**

Docket No.  
**1158.001CIP**

In Re Application Of: **Schowalter et al**

Serial No.

Filing Date

Examiner

Group Art Unit

Title: **POWDER METALLURGY CRUCIBLE FOR ALUMINUM NITRIDE CRYSTAL GROWTH**

Address to:  
**Commissioner for Patents**  
**P.O. Box 1450**  
**Alexandria, VA 22313-1450**

**37 CFR 1.97(b)**

1. ☒ The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

**37 CFR 1.97(c)**

2. ☐ The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

☐ the statement specified in 37 CFR 1.97(e);

**OR**

☐ the fee set forth in 37 CFR 1.17(p).

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**Payment of Fee**

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

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- ☒ The Director is hereby authorized to charge and credit Deposit Account No. **50-0734**  
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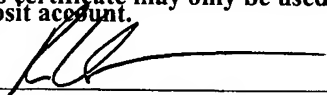
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Richard L. Sampson, Reg. 37,231  
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US

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**1158.001CIP**

Application Number

**Applicant(s)**

Schowalter et al

**Filing Date**

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INITIAL

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

**1.**

G.A. Slack and T.F. McNelly, "Growth of High Purity AlN Crystals", J. Cryst. Growth 34, 263 (1976)

**2.**

G.A. Slack and T.F. McNelly, "AlN Single Crystals"; J. Cryst. Growth 42, 560 (1977)

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**B. Raghoeamachar, M. Dudley, J.C. Rojo, K. Morgan, and L.J. Schowalter, "X-ray Characterization of Bulk AlN Single Crystals Grown by the Sublimation Technique", submitted to J. Crystal Growth (2002). Presented at Am. Assoc. Crystal Growth Conference. Seattle, WA, Aug. 2002.**

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S.V. Nagender Naidu and P. Rama Rao, Editors, "Phase Diagrams of Binary Tungsten Alloys, Indian Institute of Metals", Calcutta, pp. 7-13, (1991).

**5.**

R. Dalmau, B. Raghoeamachar, M. Dudley, R. Schlessner, and Z. Sitar, *Materials Research Society Proc.* Vol. 798, p. Y2.9.1 (2004).

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**B.M. Epelbaum, D. Hofmann, M. Bickermann, A. Winnacker, Mater. Sci. Forum 389-393, 1445 (2002).**

7.

G.A. Slack, J. Whitlock, K. Morgan, and L.J. Schowalter, Materials Research Society Proc. Vol. 798, p. Y10.74.1 (2004).

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**DATE CONSIDERED**

P09B/REV04